

**APPENDIX II**  
**PENDING CLAIMS**

14. (AMENDED) The method of claim 18, wherein the step of providing the first relative motion further comprises the step of:  
performing a chemical mechanical planarization process.

15. (AMENDED) The method of claim 18, wherein the step of providing the first relative motion further comprises the step of:  
rotating a platen supporting the polishing material.

16. (AMENDED) The method of claim 18, wherein the step of providing the second relative motion further comprises the step of:  
rotating a platen supporting the polishing material in a direction opposite a rotational direction of the first relative motion.

17. (AMENDED) The method of claim 18, wherein the step of providing the first relative motion further comprises the step of:  
moving a polishing head retaining the first substrate.

18. (AMENDED) A method for processing substrates comprising the steps of:  
providing a first relative motion between at least one substrate and a polishing material by moving the polishing head in a planar motion; and  
providing a second relative motion between at least another substrate and the polishing material.

19. (AMENDED) The method of claim 18, wherein the step of providing the first relative motion further comprises the step of:  
moving the polishing material in a linear direction.

20. (AMENDED) The method of claim 18, wherein the step of providing the first relative motion further comprises the step of:

processing additional substrates utilizing the first relative motion between the at least one substrates and the polishing material before providing the second relative motion between the at least another substrate and the polishing material.

21. The method of claim 20, wherein the step of providing the second relative motion further comprises the step of:

processing additional substrates utilizing the second relative motion between the at least another substrate and the polishing material.

22. The method of claim 20 further comprising the step of:

processing another batch of substrates utilizing the first relative motion between the substrates and the polishing material.

23. (AMENDED) The method of claim 18, wherein the first relative motion is opposite the second relative motion.

24. (AMENDED) The method of claim 18 further comprising the step of:

processing a third substrate utilizing the first relative motion.

25. (AMENDED) The method of claim 18 further comprising the step of:

flowing a temperature control fluid through passages disposed in a platen having the polishing material disposed thereon.

26. The method of claim 25, wherein the step of flowing the temperature control fluid through the platen further comprises the step of:

reducing the temperature of the polishing material.

43. (NEW) A method for processing substrates comprising the steps of:  
providing a first relative motion between at least one substrate and a polishing material by moving the polishing material in a linear direction; and  
providing a second relative motion between at least another substrate and the polishing material.
44. (NEW) The method of claim 43, wherein the step of providing the first relative motion further comprises the step of:  
performing a chemical mechanical planarization process.
45. (NEW) The method of claim 43, wherein the step of providing the first relative motion further comprises the step of:  
rotating a platen supporting the polishing material.
46. (NEW) The method of claim 43, wherein the step of providing the second relative motion further comprises the step of:  
rotating a platen supporting the polishing material in a direction opposite a rotational direction of the first relative motion.
47. (NEW) The method of claim 43, wherein the step of providing the first relative motion further comprises the step of:  
moving a polishing head retaining the first substrate.
48. (NEW) The method of claim 43, wherein the step of providing the first relative motion further comprises the step of:  
moving the polishing head in a planar motion.
49. (NEW) The method of claim 43, wherein the step of providing the first relative motion further comprises the step of:

processing additional substrates utilizing the first relative motion between the at least one substrates and the polishing material before providing the second relative motion between the at least another substrate and the polishing material.

50. (NEW) The method of claim 49, wherein the step of providing the second relative motion further comprises the step of:

processing additional substrates utilizing the second relative motion between the at least another substrate and the polishing material.

51. (NEW) The method of claim 49 further comprising the step of:

processing another batch of substrates utilizing the first relative motion between the substrates and the polishing material.

52. (NEW) The method of claim 43, wherein the first relative motion is opposite the second relative motion.

53. (NEW) The method of claim 43 further comprising the step of:

processing a third substrate utilizing the first relative motion.

54. (NEW) The method of claim 43 further comprising the step of:

flowing a temperature control fluid through passages disposed in a platen having the polishing material disposed thereon.

55. (NEW) The method of claim 54, wherein the step of flowing the temperature control fluid through the platen further comprises the step of:

reducing the temperature of the polishing material.

56. (NEW) A method for processing substrates comprising the steps of:  
providing a first relative motion between at least one substrate and a polishing material;  
providing a second relative motion between at least another substrate and the polishing material; and  
processing additional substrates utilizing the first relative motion between the at least one substrates and the polishing material before providing the second relative motion between the at least another substrate and the polishing material
57. (NEW) The method of claim 56, wherein the step of providing the first relative motion further comprises the step of:  
performing a chemical mechanical planarization process.
58. (NEW) The method of claim 56, wherein the step of providing the first relative motion further comprises the step of:  
rotating a platen supporting the polishing material.
59. (NEW) The method of claim 56, wherein the step of providing the second relative motion further comprises the step of:  
rotating a platen supporting the polishing material in a direction opposite a rotational direction of the first relative motion.
60. (NEW) The method of claim 56, wherein the step of providing the first relative motion further comprises the step of:  
moving a polishing head retaining the first substrate.
61. (NEW) The method of claim 56, wherein the step of providing the first relative motion further comprises the step of:  
moving the polishing head in a planar motion.

62. (NEW) The method of claim 56, wherein the step of providing the first relative motion further comprises the step of:

moving the polishing material in a linear direction.

63. (NEW) The method of claim 62, wherein the step of providing the second relative motion further comprises the step of:

processing additional substrates utilizing the second relative motion between the at least another substrate and the polishing material.

64. (NEW) The method of claim 62 further comprising the step of:

processing another batch of substrates utilizing the first relative motion between the substrates and the polishing material.

65. (NEW) The method of claim 56, wherein the first relative motion is opposite the second relative motion.

66. (NEW) The method of claim 56 further comprising the step of:

processing a third substrate utilizing the first relative motion.

67. (NEW) The method of claim 56 further comprising the step of:

flowing a temperature control fluid through passages disposed in a platen having the polishing material disposed thereon.

68. (NEW) The method of claim 67, wherein the step of flowing the temperature control fluid through the platen further comprises the step of:

reducing the temperature of the polishing material.